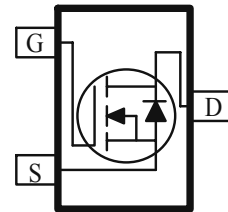
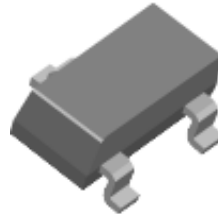


**N-Channel 30-V (D-S) MOSFET**

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ m( $\Omega$ )	$I_D$ (A)
30	60 @ $V_{GS} = 4.5V$	3.5
	82 @ $V_{GS} = 2.5V$	3.0

- Low  $r_{DS(on)}$  provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOT-23 saves board space
- Fast switching speed
- High performance trench technology



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)			
Parameter	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	
Continuous Drain Current <sup>a</sup>	$T_A = 25^\circ C$	$I_D$	3.5
	$T_A = 70^\circ C$		2.8
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	16	A
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	1.25	A
Power Dissipation <sup>a</sup>	$T_A = 25^\circ C$	$P_D$	1.3
	$T_A = 70^\circ C$		0.8
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ C$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10$ sec	100	$^\circ C/W$
	Steady-State	166	$^\circ C/W$

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

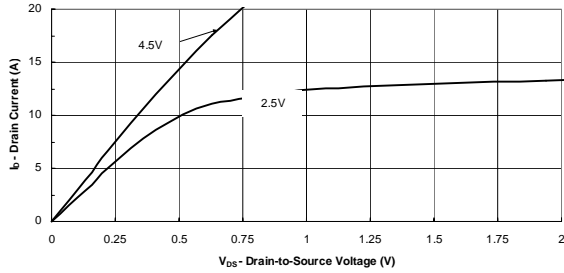
SPECIFICATIONS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
<b>Static</b>						
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	0.6			V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = 12 \text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
		$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^\circ\text{C}$			25	
On-State Drain Current <sup>A</sup>	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	6			A
Drain-Source On-Resistance <sup>A</sup>	$r_{DS(on)}$	$V_{GS} = 4.5 \text{ V}, I_D = 3.5 \text{ A}$			60	m $\Omega$
		$V_{GS} = 2.5 \text{ V}, I_D = 3 \text{ A}$			82	
Forward Transconductance <sup>A</sup>	$g_s$	$V_{DS} = 15 \text{ V}, I_D = 3.5 \text{ A}$		6.9		S
Diode Forward Voltage	$V_{SD}$	$I_S = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.8		V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 15 \text{ V}, V_{GS} = 2.5 \text{ V},$ $I_D = 3.5 \text{ A}$		6.3		nC
Gate-Source Charge	$Q_{gs}$			0.9		
Gate-Drain Charge	$Q_{gd}$			1.9		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 25 \text{ V}, R_L = 25 \Omega, I_D = 1 \text{ A},$ $V_{GEN} = 10 \text{ V}$		16		nS
Rise Time	$t_r$			5		
Turn-Off Delay Time	$t_{d(off)}$			23		
Fall-Time	$t_f$			3		

## Notes

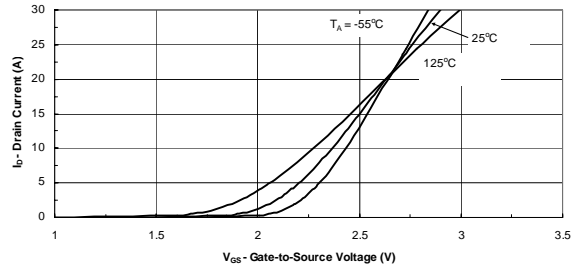
- Pulse test:  $PW \leq 300\mu\text{s}$  duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.

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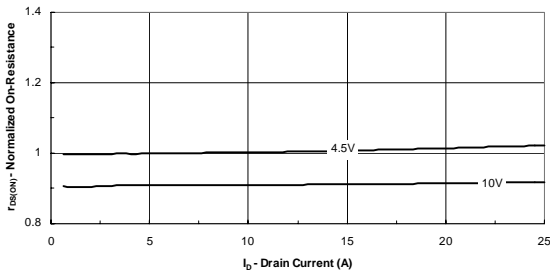
Typical Electrical Characteristics (N-Channel)



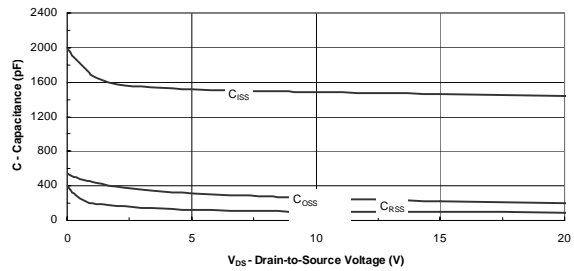
Output Characteristics



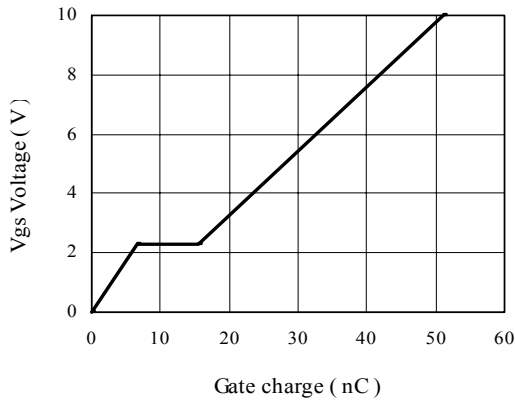
Transfer Characteristics



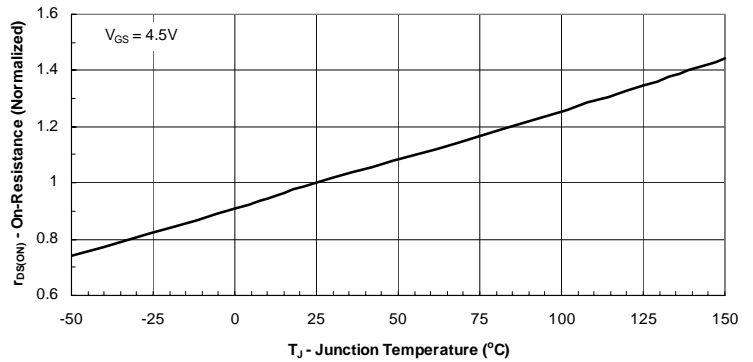
On-Resistance vs. Drain Current



Capacitance

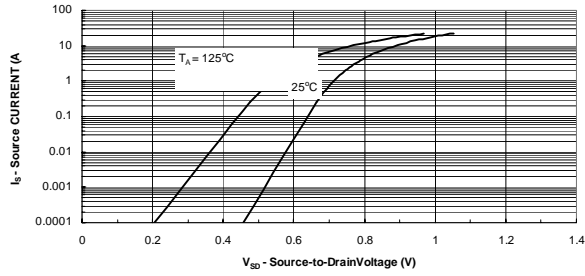


Gate Charge

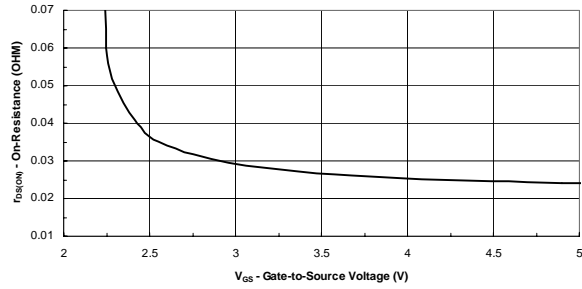


On-Resistance vs. Junction Temperature

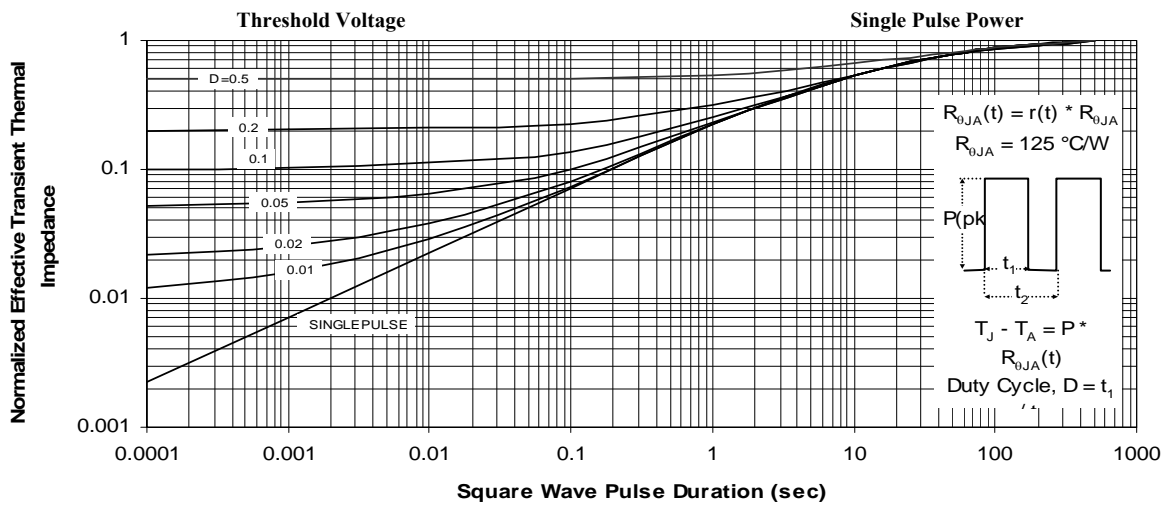
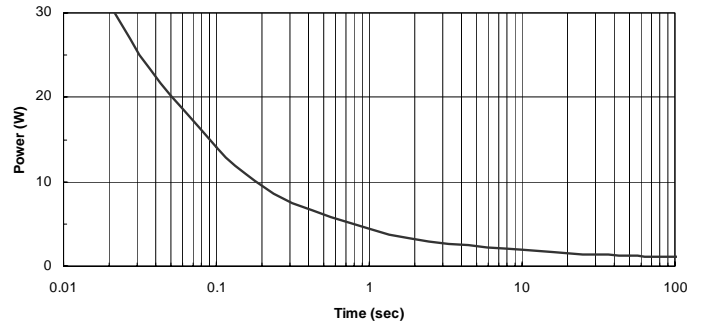
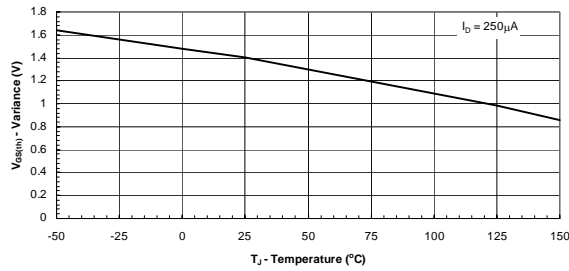
Typical Electrical Characteristics (N-Channel)



Source-Drain Diode Forward Voltage

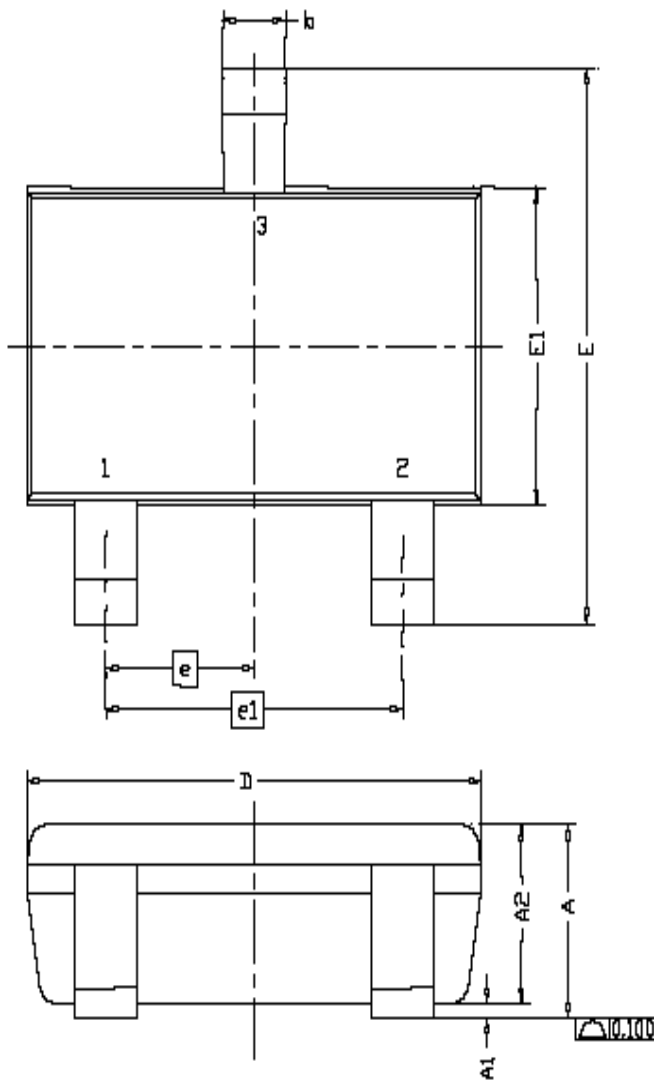


On-Resistance vs. Gate-to-Source Voltage



Normalized Thermal Transient Impedance, Junction-to-Ambient

# Package Information



DIM.	MILLIMETERS		
	MIN	NOM	MAX
A	0.935	0.95	1.10
A1	0.01	---	0.10
A2	0.85	0.90	0.925
b	0.30	0.40	0.50
c	0.10	0.15	0.25
D	2.70	2.90	3.10
E	2.60	2.80	3.00
E1	1.40	1.60	1.80
e	0.95 BSC		
e1	1.90 BSC		
L	0.30	0.40	0.60
L1	0.60REF		
L2	0.25BSC		
R	0.10	---	---
theta	0°	4°	8°
theta1	7°NOM		

